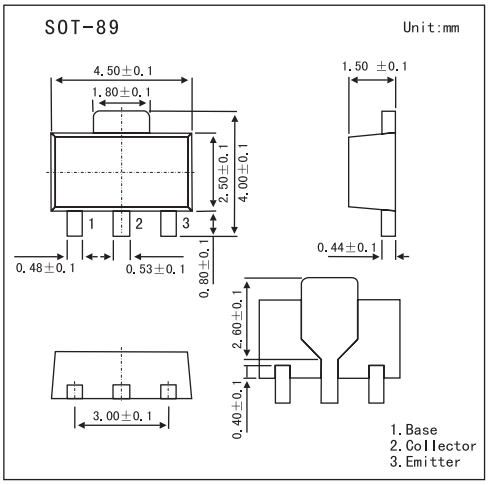
TY Semicondutor®

Product specification

2SC2883



■ Features

- Suitable For Output Stage of 3 Watts Amplifier
- Small Flat Package
- P_C = 1 to 2W (mounted on ceramic substrate)
- Complementary to 2SA1203

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	30	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1.5	A
Base Current	I_B	0.3	A
Collector Power Dissipation	P_C	500	mW
	P_C *	1000	
Jumction temperature	T_j	150	℃
Storage temperature Range	T_{stg}	-55 to +150	℃

* Mounted on a ceramic substrate (250 mm^2 x 0.8 t)

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	V_{CB} = 30V , I_E = 0			0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB} = 5V , I_C = 0			0.1	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 10mA , I_B = 0	30			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 1mA , I_C = 0	5			V
DC Current Gain	h_{FE}	V_{CE} = 2V , I_C = 500mA	100		320	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 1.5A , I_B = 0.03A			2	V
Base-Emitter Voltage	V_{BE}	V_{CE} = 2V , I_C = 500mA			1	V
Transition Frequency	f_T	V_{CE} = 2V , I_C = 500mA		120		MHz
Collector Output Capacitance	C_{ob}	V_{CB} = 10V , I_E = 0 , f = 1MHz			40	pF

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■ hFE Classification

Marking	G	
Rank	O	Y
hFE	100 ～ 200	160 ～ 320

■ Electrical Characteristics Curves